

# Sergio I. Molina

## List of Publications by Year in descending order

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200  
papers

3,349  
citations

172457

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182427

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204  
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204  
docs citations

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times ranked

4060  
citing authors

#	ARTICLE	IF	CITATIONS
1	Printable Graphene Oxide Nanocomposites as Versatile Platforms for Immobilization of Functional Biomolecules. <i>Macromolecular Materials and Engineering</i> , 2022, 307, .	3.6	6
2	STEM Tools for Semiconductor Characterization: Beyond High-Resolution Imaging. <i>Nanomaterials</i> , 2022, 12, 337.	4.1	8
3	Synthesis and Characterisation of ASA-PEEK Composites for Fused Filament Fabrication. <i>Polymers</i> , 2022, 14, 496.	4.5	4
4	Synthesis of Silver Nanocomposites for Stereolithography: In Situ Formation of Nanoparticles. <i>Polymers</i> , 2022, 14, 1168.	4.5	12
5	Structural Characterization of Al <sub>0.37</sub> In <sub>0.63</sub> N/AlN/p-Si (111) Heterojunctions Grown by RF Sputtering for Solar Cell Applications. <i>Materials</i> , 2021, 14, 2236.	2.9	0
6	Additive Manufacturing of Gold Nanostructures Using Nonlinear Photoreduction under Controlled Ionic Diffusion. <i>International Journal of Molecular Sciences</i> , 2021, 22, 7465.	4.1	2
7	Modification of the Mechanical Properties of Core-Shell Liquid Gallium Nanoparticles by Thermal Oxidation at Low Temperature. <i>Particle and Particle Systems Characterization</i> , 2021, 38, 2100141.	2.3	3
8	Investigation on Sb distribution for InSb/InAs sub-monolayer heterostructure using TEM techniques. <i>Nanotechnology</i> , 2020, 31, 025706.	2.6	5
9	Effect of the cap layer growth temperature on the Sb distribution in InAs/InSb/InAs sub-monolayer heterostructures for mid-infrared devices. <i>Nanotechnology</i> , 2020, 31, 105702.	2.6	1
10	Design of a Bio-Based Device for Micro Total Analysis Combining Fused Deposition Modeling and Layer-by-Layer Technologies. <i>Macromolecular Materials and Engineering</i> , 2020, 305, 2000461.	3.6	2
11	Synthesis and Characterisation of Acrylic Resin-Al Powder Composites Suitable for Additive Manufacturing. <i>Polymers</i> , 2020, 12, 1642.	4.5	5
12	Influence of the Degree of Cure in the Bulk Properties of Graphite Nanoplatelets Nanocomposites Printed via Stereolithography. <i>Polymers</i> , 2020, 12, 1103.	4.5	21
13	Development of carbon fiber acrylonitrile styrene acrylate composite for large format additive manufacturing. <i>Materials and Design</i> , 2020, 191, 108577.	7.0	30
14	Heterometallic Titanium-Organic Frameworks by Metal-Induced Dynamic Topological Transformations. <i>Journal of the American Chemical Society</i> , 2020, 142, 6638-6648.	13.7	40
15	A sugar-beet waste based thermoplastic agro-composite as substitute for raw materials. <i>Journal of Cleaner Production</i> , 2020, 257, 120382.	9.3	23
16	Au-NiO nanocomposite for hot electron-assisted plasmonic photocatalysis. <i>Journal of Materials Chemistry C</i> , 2020, 8, 9885-9897.	5.5	11
17	Materials with enhanced adhesive properties based on acrylonitrile-butadiene-styrene (ABS)/thermoplastic polyurethane (TPU) blends for fused filament fabrication (FFF). <i>Materials and Design</i> , 2019, 182, 108044.	7.0	88
18	Optical properties of metamorphic type-I In <sub>x</sub> Sb <sub>x</sub> /Al <sub>y</sub> In <sub>1-y</sub> As quantum wells grown on GaAs for the mid-infrared spectral range. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 465102.	2.8	7

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19	High Spatial Resolution Mapping of Localized Surface Plasmon Resonances in Single Gallium Nanoparticles. <i>Small</i> , 2019, 15, 1902920.	10.0	8
20	Room-temperature Operation of Low-voltage, Non-volatile, Compound-semiconductor Memory Cells. <i>Scientific Reports</i> , 2019, 9, 8950.	3.3	17
21	Effect of the thermal annealing and the nominal composition in the elemental distribution of $\text{In}_x\text{Al}_{1-x}\text{As}_y\text{Sb}_{1-y}$ for triple junction solar cells. <i>Journal of Alloys and Compounds</i> , 2019, 792, 1021-1027.	5.5	2
22	Development of Surface-Coated Polylactic Acid/Polyhydroxyalkanoate (PLA/PHA) Nanocomposites. <i>Polymers</i> , 2019, 11, 400.	4.5	29
23	Large-format fused deposition additive manufacturing: a review. <i>Rapid Prototyping Journal</i> , 2019, 26, 793-799.	3.2	24
24	Inhibition of light emission from the metastable tetragonal phase at low temperatures in island-like films of lead iodide perovskites. <i>Nanoscale</i> , 2019, 11, 22378-22386.	5.6	4
25	Modified qHAADF method for atomic column-by-column compositional quantification of semiconductor heterostructures. <i>Journal of Materials Science</i> , 2019, 54, 3230-3241.	3.7	5
26	Influence of the crosstalk on the intensity of HAADF-STEM images of quaternary semiconductor materials. <i>Journal of Microscopy</i> , 2019, 273, 81-88.	1.8	3
27	Structural characterization of bulk and nanoparticle lead halide perovskite thin films by (S)TEM techniques. <i>Nanotechnology</i> , 2019, 30, 135701.	2.6	5
28	DESIGN AND DEVELOPMENT OF A PARAMETRIZABLE ELECTRIC GUITAR THROUGH ADDITIVE MANUFACTURING. <i>Dyna (Spain)</i> , 2019, 94, 26-31.	0.2	1
29	Gaussian kernel density functions for compositional quantification in atom probe tomography. <i>Materials Characterization</i> , 2018, 139, 63-69.	4.4	3
30	Geometric-Structural Study of the Accelerated Degradation of Mold Cavities for HDPE Injection. <i>Journal of Failure Analysis and Prevention</i> , 2018, 18, 55-65.	0.9	0
31	Analysis of Bi Distribution in Epitaxial GaAsBi by Aberration-Corrected HAADF-STEM. <i>Nanoscale Research Letters</i> , 2018, 13, 125.	5.7	12
32	Influence of the AlN interlayer thickness on the photovoltaic properties of in-rich AlInN on Si heterojunctions deposited by RF sputtering. <i>AIP Advances</i> , 2018, 8, .	1.3	6
33	Exploring the Capability of HAADF-STEM Techniques to Characterize Graphene Distribution in Nanocomposites by Simulations. <i>Journal of Nanomaterials</i> , 2018, 2018, 1-12.	2.7	0
34	Structural and chemical characterization of CdSe-ZnS core-shell quantum dots. <i>Applied Surface Science</i> , 2018, 457, 93-97.	6.1	22
35	Influence of the growth temperature on the composition distribution at sub-nm scale of $\text{InAlAsSb}$ for solar cells. <i>Journal of Alloys and Compounds</i> , 2018, 763, 1005-1011.	5.5	4
36	Large-format polymeric pellet-based additive manufacturing for the naval industry. <i>Additive Manufacturing</i> , 2018, 23, 79-85.	3.0	57

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37	HAADF-STEM for the analysis of core-shell quantum dots. Journal of Materials Science, 2018, 53, 15226-15236.	3.7	5
38	Quality improvement of AlInN/p-Si heterojunctions with AlN buffer layer deposited by RF-sputtering. Journal of Alloys and Compounds, 2018, 769, 824-830.	5.5	15
39	Influence of the addition of graphene-like materials on the properties of polyamide for Powder Bed Fusion. Progress in Additive Manufacturing, 2018, 3, 233-244.	4.8	6
40	Comparison of the thickness determined by Fresnel contrast and Rutherford backscattering spectrometry in ultra-thin layers. , 2018, , 305-308.		0
41	Multiple atomic configurations of inversion domain boundaries in GaN grown on (111)Si. , 2018, , 333-336.		0
42	Effect of an in-situ thermal annealing on the structural properties of self-assembled GaSb/GaAs quantum dots. Applied Surface Science, 2017, 395, 136-139.	6.1	4
43	Effect of annealing on the compositional modulation of InAlAsSb. Applied Surface Science, 2017, 395, 105-109.	6.1	2
44	Size effect and scaling power-law for superelasticity in shape-memory alloys at the nanoscale. Nature Nanotechnology, 2017, 12, 790-796.	31.5	70
45	Structural characterization of InAlAsSb/InGaAs/InP heterostructures for solar cells. Applied Surface Science, 2017, 395, 98-104.	6.1	5
46	Structural and Compositional Analysis of Core/Shell QDs by Transmission Electron Microscopy Techniques. Microscopy and Microanalysis, 2017, 23, 1768-1769.	0.4	0
47	Wide bandgap, strain-balanced quantum well tunnel junctions on InP substrates. Journal of Applied Physics, 2016, 119, 194503.	2.5	4
48	Atomic-column scanning transmission electron microscopy analysis of misfit dislocations in GaSb/GaAs quantum dots. Journal of Materials Science, 2016, 51, 7691-7698.	3.7	9
49	HAADF-STEM analysis of the composition distribution in InAlAsSb/InGaAs/InP layers for solar cells applications. Microscopy and Microanalysis, 2016, 22, 30-31.	0.4	2
50	Structural Quality of GaSb/GaAs Quantum Dots for Solar Cells Analyzed by Electron Microscopy Techniques. Microscopy and Microanalysis, 2016, 22, 38-39.	0.4	0
51	Small-pore driven high capacitance in a hierarchical carbon via carbonization of Ni-MOF-74 at low temperatures. Chemical Communications, 2016, 52, 9141-9144.	4.1	51
52	Atom-scale compositional distribution in InAlAsSb-based triple junction solar cells by atom probe tomography. Nanotechnology, 2016, 27, 305402.	2.6	13
53	Atom probe tomography analysis of InAlGaAs capped InAs/GaAs stacked quantum dots with variable barrier layer thickness. Acta Materialia, 2016, 103, 651-657.	7.9	6
54	CVD synthesis of carbon spheres using NiFe-LDHs as catalytic precursors: structural, electrochemical and magnetoresistive properties. Journal of Materials Chemistry C, 2016, 4, 440-448.	5.5	22

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55	Molecular beam epitaxy of InAlAsSb for the top cell in high-efficiency InP-based lattice-matched triple-junction solar cells. , 2015, , .		2
56	Determination of Local Chemistry Composition of Low-Dimensional Semiconductor Nanostructures Through the use of High-Resolution HAADF images. Microscopy and Microanalysis, 2015, 21, 2083-2084.	0.4	0
57	High spatial resolution mapping of individual and collective localized surface plasmon resonance modes of silver nanoparticle aggregates: correlation to optical measurements. Nanoscale Research Letters, 2015, 10, 1024.	5.7	12
58	Mapping the plasmonic response of gold nanoparticles embedded in TiO <sub>2</sub> thin films. Nanotechnology, 2015, 26, 405702.	2.6	3
59	Delta doping and positioning effects of type II GaSb quantum dots in GaAs solar cell. Materials Research Innovations, 2015, 19, 512-516.	2.3	6
60	3D compositional analysis at atomic scale of InAlGaAs capped InAs/GaAs QDs. Scripta Materialia, 2015, 103, 73-76.	5.2	12
61	Effect of doping on the morphology of GaSb/GaAs nanostructures for solar cells. Applied Surface Science, 2015, 359, 676-678.	6.1	1
62	Preferential sites for InAsP/InP quantum wire nucleation using molecular dynamics. European Physical Journal B, 2014, 87, 1.	1.5	0
63	Modeling, design and experimental results for high efficiency multi-junction solar cells lattice matched to InP. Proceedings of SPIE, 2014, , .	0.8	6
64	Charge transfer interactions in self-assembled single walled carbon nanotubes/Dawsonâ€™Wells polyoxometalate hybrids. Chemical Science, 2014, 5, 4346-4354.	7.4	49
65	Analysis of electron beam damage of exfoliated MoS <sub>2</sub> sheets and quantitative HAADF-STEM imaging. Ultramicroscopy, 2014, 146, 33-38.	1.9	63
66	A methodology for the extraction of quantitative information from electron microscopy images at the atomic level. Journal of Physics: Conference Series, 2014, 522, 012013.	0.4	3
67	Defect reduction in heteroepitaxial InP on Si by epitaxial lateral overgrowth. Materials Express, 2014, 4, 41-53.	0.5	7
68	Transmission Electron Microscopy of 1D-Nanostructures. , 2014, , 657-701.		0
69	High spatial resolution mapping of surface plasmon resonance modes in single and aggregated gold nanoparticles assembled on DNA strands. Nanoscale Research Letters, 2013, 8, 337.	5.7	18
70	Influence of RF-sputtering power on formation of vertically stacked Si <sub>1-x</sub> Ge <sub>x</sub> nanocrystals between ultra-thin amorphous Al <sub>2</sub> O <sub>3</sub> layers: structural and photoluminescence properties. Journal Physics D: Applied Physics, 2013, 46, 385301.	2.8	1
71	Strain analysis for the prediction of the preferential nucleation sites of stacked quantum dots by combination of FEM and APT. Nanoscale Research Letters, 2013, 8, 513.	5.7	3
72	Extreme voltage recovery in GaAs:Ti intermediate band solar cells. Solar Energy Materials and Solar Cells, 2013, 108, 175-179.	6.2	22

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73	Towards high efficiency multi-junction solar cells grown on InP Substrates. , 2013, , .		7
74	Fabrication of Needle-Shaped Specimens Containing Subsurface Nanostructures for Electron Tomography. Lecture Notes in Nanoscale Science and Technology, 2013, , 241-266.	0.8	0
75	Compositional analysis of InAs-GaAs-GaSb heterostructures by Low-Loss Electron Energy Loss Spectroscopy. Journal of Physics: Conference Series, 2013, 471, 012012.	0.4	2
76	Quantitative study of the interfacial intermixing and segregation effects across the wetting layer of Ga(As,Sb)-capped InAs quantum dots. Applied Physics Letters, 2012, 101, .	3.3	4
77	Tuning the properties of Ge-quantum dots superlattices in amorphous silica matrix through deposition conditions. Journal of Applied Physics, 2012, 111, 074316.	2.5	4
78	Quantification of corrugation in simulated graphene by electron tomography techniques. Applied Physics Letters, 2012, 101, 213106.	3.3	1
79	(Invited) Photoluminescence Excitation Spectroscopy of Si Nanocrystals in SiO <sub>2</sub> . ECS Transactions, 2012, 45, 3-8.	0.5	0
80	Production of Nanometer-Size GaAs Nanocrystals by Nanosecond Laser Ablation in Liquid. Journal of Nanoscience and Nanotechnology, 2012, 12, 6774-6778.	0.9	24
81	Initial Results from a 200 kV UltraSTEM. Microscopy and Microanalysis, 2012, 18, 326-327.	0.4	0
82	Investigation of saturation and excitation behavior of 1.5 $\mu$ m emission from Er <sup>3+</sup> ions in SiO <sub>2</sub> sensitized with Si nanocrystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2312-2317.	0.8	3
83	InAs/AlGaAs quantum dot intermediate band solar cells with enlarged sub-bandgaps. , 2012, , .		25
84	Analysis of the 3D distribution of stacked self-assembled quantum dots by electron tomography. Nanoscale Research Letters, 2012, 7, 681.	5.7	3
85	Cubic and hexagonal InGaAsN dilute arsenides by unintentional homogeneous incorporation of As into InGaN. Scripta Materialia, 2012, 66, 351-354.	5.2	1
86	A methodology for the fabrication by FIB of needle-shape specimens around sub-surface features at the nanometre scale. Micron, 2012, 43, 643-650.	2.2	15
87	High-Resolution Electron Microscopy of Semiconductor Heterostructures and Nanostructures. Springer Series in Materials Science, 2012, , 23-62.	0.6	2
88	Distribution of bismuth atoms in epitaxial GaAsBi. Applied Physics Letters, 2011, 98, 101902.	3.3	38
89	Light Emission from Nanocrystalline Si Inverse Opals and Controlled Passivation by Atomic Layer Deposited Al <sub>2</sub> O <sub>3</sub> . Advanced Materials, 2011, 23, 5219-5223.	21.0	17
90	Formation and Emission Properties of Single InGaAs <sup>+</sup> GaAs Quantum Dots and Pairs Grown by Droplet Epitaxy. AIP Conference Proceedings, 2011, , .	0.4	0

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91	Three dimensional atom probe imaging of GaAsSb quantum rings. Ultramicroscopy, 2011, 111, 1073-1076.	1.9	14
92	Structural characterization of GaSb-capped InAs/GaAs quantum dots with a GaAs intermediate layer. Materials Letters, 2011, 65, 1608-1610.	2.6	4
93	Novel Method of Preparation of Gold Nanoparticle Doped TiO <sub>2</sub> and SiO <sub>2</sub> Plasmonic Thin Films: Optical Characterization and Comparison with Maxwell Garnett Modeling. Advanced Functional Materials, 2011, 21, 3502-3507.	14.9	55
94	Strain balanced quantum posts. Applied Physics Letters, 2011, 98, 173106.	3.3	7
95	Tuning the properties of exciton complexes in self-assembled GaSb/GaAs quantum rings. Physical Review B, 2011, 83, .	3.2	34
96	Compositional Analysis with Atomic Column Spatial Resolution by 5th-Order Aberration-Corrected Scanning Transmission Electron Microscopy. Microscopy and Microanalysis, 2011, 17, 578-581.	0.4	16
97	Seeing inside materials by aberration-corrected electron microscopy. International Journal of Nanotechnology, 2011, 8, 935.	0.2	0
98	Calculation of integrated intensities in aberration-corrected Z-contrast images. Journal of Electron Microscopy, 2011, 60, 29-33.	0.9	20
99	Aberration-corrected scanning transmission electron microscopy of nanostructures for photovoltaics. , 2011, , .		0
100	Structural Origin of Enhanced Luminescence Efficiency of Antimony Irradiated InAs Quantum Dots. Advanced Science Letters, 2011, 4, 3776-3778.	0.2	0
101	Through-focal HAADF-STEM of buried nanostructures. Journal of Physics: Conference Series, 2010, 209, 012032.	0.4	1
102	Theoretical modelling of quaternary GaInAsSb/GaAs self-assembled quantum dots. Journal of Physics: Conference Series, 2010, 245, 012081.	0.4	4
103	Growth of Low-Density Vertical Quantum Dot Molecules with Control in Energy Emission. Nanoscale Research Letters, 2010, 5, 1913-1916.	5.7	7
104	Effect of annealing on the structural and optical properties of (311)B GaAsBi layers. Applied Surface Science, 2010, 256, 5688-5690.	6.1	16
105	Transmission electron microscopy study of vertical quantum dots molecules grown by droplet epitaxy. Applied Surface Science, 2010, 256, 5659-5661.	6.1	4
106	Lateral absorption measurements of InAs/GaAs quantum dots stacks: Potential as intermediate band material for high efficiency solar cells. Energy Procedia, 2010, 2, 27-34.	1.8	2
107	<math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.gif" display="inline" overflow="scroll"><math>\langle msub \rangle \langle mrow \rangle \langle mstyle		

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109	Surface nanostructuring of $\text{TiO}_2$ films by high energy ion irradiation. Physical Review B, 2010, 82, .		
110	Publisher's Note: Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots [Phys. Rev. B82, 235316 (2010)]. Physical Review B, 2010, 82, .	3.2	0
111	Reducing carrier escape in the InAs/GaAs quantum dot intermediate band solar cell. Journal of Applied Physics, 2010, 108, .	2.5	156
112	Exploring semiconductor quantum dots and wires by high resolution electron microscopy. Journal of Physics: Conference Series, 2010, 209, 012004.	0.4	2
113	Blocking of indium incorporation by antimony in III-V-Sb nanostructures. Nanotechnology, 2010, 21, 145606.	2.6	16
114	Morphological evolution of InAs/InP quantum wires through aberration-corrected scanning transmission electron microscopy. Nanotechnology, 2010, 21, 325706.	2.6	5
115	Strain balanced quantum posts for intermediate band solar cells. , 2010, , .		2
116	Microstructural improvements of InP on GaAs (001) grown by molecular beam epitaxy by in situ hydrogenation and postgrowth annealing. Applied Physics Letters, 2009, 94, 041919.	3.3	10
117	High resolution electron microscopy of GaAs capped GaSb nanostructures. Applied Physics Letters, 2009, 94, .	3.3	17
118	Aberration-corrected scanning transmission electron microscopy: from atomic imaging and analysis to solving energy problems. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2009, 367, 3709-3733.	3.4	89
119	Column-by-column compositional mapping by Z-contrast imaging. Ultramicroscopy, 2009, 109, 172-176.	1.9	68
120	A comparison of ZnMgSSe and MgS wide bandgap semiconductors used as barriers: Growth, structure and luminescence properties. Journal of Crystal Growth, 2009, 311, 2099-2101.	1.5	9
121	Accuracy assessment of strain mapping from Z-contrast images of strained nanostructures. Applied Physics Letters, 2009, 95, .	3.3	16
122	Formation of Spatially Addressed Ga(As)Sb Quantum Rings on GaAs(001) Substrates by Droplet Epitaxy. Crystal Growth and Design, 2009, 9, 1216-1218.	3.0	10
123	Carrier localization in GaBiAs probed by photomodulated transmittance and photoluminescence. Journal of Applied Physics, 2009, 106, 023518.	2.5	55
124	Photomodulated transmittance of GaBiAs layers grown on (001) and (311)B GaAs substrates. Microelectronics Journal, 2009, 40, 537-539.	2.0	9
125	Aqueous Near-Infrared Fluorescent Composites Based on Apoferritin-Encapsulated PbS Quantum Dots. Advanced Materials, 2008, 20, 3592-3596.	21.0	79
126	Carrier recombination effects in strain compensated quantum dot stacks embedded in solar cells. Applied Physics Letters, 2008, 93, 123114.	3.3	46



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127	Stress compensation by GaP monolayers for stacked InAs/GaAs quantum dots solar cells. Conference Record of the IEEE Photovoltaic Specialists Conference, 2008, , .	0.0	0
128	Point Defect Configurations of Supersaturated Au Atoms Inside Si Nanowires. Nano Letters, 2008, 8, 1016-1019.	9.1	119
129	HAADF-STEM image simulation of large scale nanostructures. , 2008, , 111-112.		0
130	Simulation of high angle annular dark field scanning transmission electron microscopy images of large nanostructures. Applied Physics Letters, 2008, 93, 153107.	3.3	43
131	Experimental and Simulated Strain Field Maps in Stacked Quantum Wires. Microscopy and Microanalysis, 2008, 14, 344-345.	0.4	4
132	A Method to Determine the Strain and Nucleation Sites of Stacked Nano-Objects. Journal of Nanoscience and Nanotechnology, 2008, 8, 3422-3426.	0.9	11
133	PPA: An Improved Implementation of Peak Pairs procedure as a DM plug-in for Strain Mapping. , 2008, , 125-126.		0
134	TEM characterization of InAs/GaAs quantum dots capped by a GaSb/GaAs layer. , 2008, , 45-46.		0
135	A TEM study of the evolution of InAs/GaAs self-assembled dots on (311)B GaAs with growth interruption. Semiconductor Science and Technology, 2007, 22, 168-170.	2.0	3
136	Direct imaging of quantum wires nucleated at diatomic steps. Applied Physics Letters, 2007, 91, 143112.	3.3	17
137	Molecular beam epitaxy of GaBiAs on (311)B GaAs substrates. Applied Physics Letters, 2007, 91, 251909.	3.3	50
138	Critical strain region evaluation of self-assembled semiconductor quantum dots. Nanotechnology, 2007, 18, 475503.	2.6	19
139	Error Quantification in Strain Mapping Methods. Microscopy and Microanalysis, 2007, 13, 320-328.	0.4	20
140	Excitons in coupled InAs <sup>+</sup> InP self-assembled quantum wires. Physical Review B, 2007, 75, .	3.2	25
141	Incorporation of Sb in InAs <sup>+</sup> GaAs quantum dots. Applied Physics Letters, 2007, 91, 263105.	3.3	29
142	The Peak Pairs algorithm for strain mapping from HRTEM images. Ultramicroscopy, 2007, 107, 1186-1193.	1.9	230
143	Determination of the strain generated in InAs/InP quantum wires: prediction of nucleation sites. Nanotechnology, 2006, 17, 5652-5658.	2.6	30
144	Direct experimental evidence of metastable epitaxial zinc-blende MgS. Applied Physics Letters, 2006, 89, 121907.	3.3	12

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145	Room temperature emission at 1.6 $\mu$ m from InGaAs quantum dots capped with GaAsSb. Applied Physics Letters, 2005, 87, 202108.	3.3	106
146	Strain mapping from HRTEM images. , 2005, , 191-194.		1
147	Vertical order in stacked layers of self-assembled In(Ga)As quantum rings on GaAs (001). Applied Physics Letters, 2005, 86, 071918.	3.3	71
148	Quantification of the influence of TEM operation parameters on the error of HREM image matching. , 2005, , 195-198.		0
149	Stacking of InAs/InP(001) quantum wires studied by in situ stress measurements: Role of inhomogeneous stress fields. Applied Physics Letters, 2004, 84, 4723-4725.	3.3	31
150	Emission wavelength engineering of InAs/InP(001) quantum wires. European Physical Journal B, 2004, 40, 433-437.	1.5	12
151	Structural Study of Micro and Nanotubes Synthesized by Rapid Thermal Chemical Vapor Deposition. Mikrochimica Acta, 2004, 145, 129-132.	5.0	4
152	Crystalline Inclusions Formed in C+N+BF <sub>2</sub> Coimplanted on Silicon (111). Mikrochimica Acta, 2004, 145, 165-169.	5.0	0
153	Microchemical Analysis and Microstructural Development of Cr-Doped Mullites. Mikrochimica Acta, 2004, 145, 255-260.	5.0	5
154	The role of Ge predeposition temperature in the MBE epitaxy of SiC on Silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 341-346.	0.8	10
155	Size control of InAs/InP(001) quantum wires by tailoring As exchange. Applied Physics Letters, 2004, 85, 1424-1426.	3.3	38
156	Estudio por microscopía electrónica y espectroscopía de infra-rojos de capas de SiC obtenidas mediante carburización de obleas de Si. Boletín De La Sociedad Española De Cerámica Y Vidrio, 2004, 43, 363-366.	1.9	1
157	N+BF <sub>2</sub> and N+C+BF <sub>2</sub> high-dose co-implantation in silicon. Applied Physics A: Materials Science and Processing, 2003, 76, 791-800.	2.3	3
158	Size self-filtering effect in vertical stacks of InAs/InP self-assembled quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 174-176.	2.7	3
159	Transmission electron microscopy study of ultra-thin SiC layers obtained by rapid thermal carbonization of Si wafers. Physica Status Solidi A, 2003, 195, 116-121.	1.7	2
160	High Reflectivity AlGaIn/AlN DBR Mirrors Grown by PA-MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 258-262.	0.8	8
161	Transmission electron microscopy study of simultaneous high-dose C++N+ co-implantation into (111)Si. Thin Solid Films, 2003, 426, 16-30.	1.8	3
162	HRTEM study of Al <sub>x</sub> Ga <sub>1-x</sub> N/AlN DBR mirrors. Diamond and Related Materials, 2003, 12, 1178-1181.	3.9	5

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163	SiC voids, mosaic microstructure and dislocations distribution in Si carbonized layers. Diamond and Related Materials, 2003, 12, 1227-1230.	3.9	18
164	Size and critical thickness evolution during growth of stacked layers of InAs/InP(001) quantum wires studied by in situ stress measurements. Materials Research Society Symposia Proceedings, 2003, 794, 154.	0.1	1
165	Correlation Between the AlN Buffer Layer Thickness and the GaN Polarity in GaN/AlN/Si(111) Grown by MBE. Materials Research Society Symposia Proceedings, 2002, 743, L3.25.1.	0.1	0
166	Size-filtering effects by stacking InAs/InP (001) self-assembled quantum wires into multilayers. Physical Review B, 2002, 65, .	3.2	25
167	Origin of Inversion Domains in GaN/AlN/Si(111) Heterostructures Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2002, 234, 935-938.	1.5	4
168	Filtering Study of Threading Dislocations in AlN Buffered MBE GaN/Sapphire Using Single and Multiple High Temperature AlN Intermediate Layers. Physica Status Solidi A, 2002, 192, 424-429.	1.7	0
169	AlN buffer layer thickness influence on inversion domains in GaN/AlN/Si(111). Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 181-184.	3.5	8
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